An experimental study of diffusion welded contacts to p-type silicon carbide
Korolkov, Oleg Telekommunikatsioon 2002 : IX rahvusvahelise telekommunikatsioonipäeva materjalid 2002 / lk. 21-23 : ill

Analysis of deep level centers in GaAs pin-diode structures
Korolkov, Oleg; **Toompuu, Jana**; **Rang, Toomas** Elektronika ir elektrotechnika = Electronics and electrical engineering 2013 / [4 p.] : ill https://doi.org/10.5755/j01.eee.19.10.5903 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Analysis of deep level spectrum in GaAs p+-p-i-n-n+ structures
Toompuu, Jana; **Sleptšuk, Natalja**; **Korolkov, Oleg**; **Rang, Toomas** Materials characterization VII 2015 / p. 283-294 : ill

Analysis of the basic Schottky parameters for diffusion-welded aluminium contacts to p- and n-type SiC
Korolkov, Oleg; **Ljutov, Jevgeni**; Kuznetsova, Natalja; Ruut, Jana; **Rang, Toomas** BEC 2004 : proceedings of the 9th Biennial Baltic Electronics Conference : October 3-6, 2004, Tallinn, Estonia 2004 / p. 51-53 : ill

The basic Schottky parameters for combined diffusion welded and sputter metal contacts
Kuznetsova, Natalja; **Korolkov, Oleg**; **Rang, Toomas**; **Pikkov, Mihhail** BEC 2006 : 2006 International Baltic Electronics Conference : Tallinn University of Technology, October 2-4, 2006, Tallinn, Estonia : proceedings of the 10th Biennial Baltic Electronics Conference 2006 / p. 47-50 : ill

Change in the parameters of electron-irradiated 4H-SIC Schottky diodes as a function of the time during low-temperature isothermal annealing
Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja**; **Rang, Toomas** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018,Birmingham, UK 2019 / p. 734-737 https://doi.org/10.4028/www.scientific.net/MSF.963.734 Conference proceeding at Scopus Article at Scopus

Clamp mode package diffusion welded power SiC Schottky diodes
Korolkov, Oleg; **Kuznetsova, Natalja**; **Rang, Toomas** BEC 2006 : 2006 International Baltic Electronics Conference : Tallinn University of Technology, October 2-4, 2006, Tallinn, Estonia : proceedings of the 10th Biennial Baltic Electronics Conference 2006 / p. 55-58 : ill

Comparative characteristics of 6H- and 4H-SiC surfaces in diffusion welding
Korolkov, Oleg; **Rang, Toomas** Proceedings of the Estonian Academy of Sciences. Engineering 2001 / 4, p. 347-353 : ill

Comparative characteristics of diffusion welded Al contacts to 6H- and 4H-SiC substrates
Korolkov, Oleg; **Rang, Toomas** The 7th Biennial Conference on Electronics and Microsystem Technology "Baltic Electronics Conference" : BEC 2000 : October 8 - 11, 2000, Tallinn, Estonia : conference proceedings 2000 / p. 23-26 : ill

Comparative characteristics of diffusion-welded high-voltage stacks and connected in series Schottky diodes
Sleptšuk, Natalja; **Korolkov, Oleg**; **Land, Raul**; **Toompuu, Jana**; **Annus, Paul**; **Rang, Toomas** BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 39-42 : ill http://www.ester.ee/record=b2150914*est

Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application
Sleptšuk, Natalja; Lebedev, Alexander A.; Eliseyev, Ilya; **Korolkov, Oleg**; **Toompuu, Jana**; **Land, Raul**; **Mikli, Valdek**; Zubov, Alexander; **Rang, Toomas** Modern Materials and Manufacturing 2019 : 12th International DAAAM Baltic Conference and 27th International Baltic Conference BALTMATTRIB 2019. Selected, peer reviewed papers from the conference Modern Materials and Manufacturing 2019 (MMM 2019), April 24-26, 2019, Tallinn, Estonia 2019 / p. 185-190 : ill https://www.ester.ee/record=b5235278*est https://www.scientific.net/KEM.799.185 https://doi.org/10.4028/www.scientific.net/KEM.799.185 Conference proceeding at Scopus Article at Scopus

Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons
Kozlovski, Vitali V.; **Korolkov, Oleg**; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja** Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 https://doi.org/10.4028/www.scientific.net/MSF.1004.231 Conference Proceedings at Scopus Article at Scopus

Comparison of individual SiC JBS chips and JBS stacks connected in series by diffusion welding
Sleptšuk, Natalja; **Korolkov, Oleg**; **Toompuu, Jana**; **Rang, Toomas** BEC 2010 : 2010 12th Biennial Baltic Electronics Conference : proceedings of the 12th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 4-6, 2010, Tallinn, Estonia 2010 / p. 81-84 : ill

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons
Lebedev, Alexander A.; Davidovskaja, Klavdia; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Toompuu, Jana** Silicon

Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 447-450 : ill https://doi.org/10.4028/www.scientific.net/MSF.897.447 Conference proceedings at Scopus Article at Scopus

Degragation of 600-V 4H-SiC Schottky diodes under irradation with 0,9 MeV electrons
Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Dependence of the carrier removal rate in 4H-SIC PN structures on irradiation temperature
Lebedev, Alexander A.; Davydovskaya, Klavdya S.; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptsuk, Natalja**; **Toompuu, Jana** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018,Birmingham, UK 2019 / p. 730-733 https://doi.org/10.4028/www.scientific.net/MSF.963.730 Conference proceeding at Scopus Article at Scopus

Diffusion welded Al contacts to p-type SiC
Korolkov, Oleg; **Rang, Toomas**; Syrkin, A.; Dmitriev, V. Silicon Carbide and Related Materials 2002 : ECSCRM2002 2003 / p. 697-700 https://www.scientific.net/MSF.433-436.697

Diffusion welded contacts and related art applied to semiconductor materials
Korolkov, Oleg; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Elektronika ir elektrotechnika = Electronics and electrical engineering 2011 / p. 67-70 : ill https://eejournal.ktu.lt/index.php/elt/article/view/359

Diffusion welded contacts for silicon semiconductor devices
Korolkov, Oleg; **Rang, Toomas** Proceedings of the International Conference and Exhibition Micro Materials : MicroMat '97, April 16-18, 1997, Berlin, Germany 1997 / p. 1035-1037

The diffusion welded contacts in power electronics
Korolkov, Oleg; **Rang, Toomas** BEC : Baltic Electronics Conference : proceedings of the 4th Biennial Conference, October 9-14, 1994, Tallinn (Estonia). 2 1994 / p. 573-578: ill https://www.ester.ee/record=b2150914*est

Diffusion welding contacts to 6H-SiC substrates
Korolkov, Oleg; **Rang, Toomas** 43. Internationales Wissenschaftliches Kolloquium, 21.-24.09.1998 1998 / p. 47-48

Diffusion welding techniques for power SiC Schottky packaging
Korolkov, Oleg; **Rang, Toomas**; Syrkin, A.; Dmitriev, V. Silicon carbide and related materials 2005 2006 / p. 919-922

Diffusion welding techniques for power SiC Schottky packaging
Korolkov, Oleg; **Rang, Toomas**; Syrkin, A.; Dmitriev, V. Final programm of the 12th International Conference on Silicon Carbide and Related Materials : ICSCRM2005 : Pittsburgh, PA, USA 2005 / p. 71

Diffusion welding technology as a method of metallization of ceramic substrates
Korolkov, Oleg; **Rang, Toomas** BEC'96 : the 5th Biennial Baltic Electronics Conference, October 7-11, 1996, Tallinn, Estonia : proceedings 1996 / p. 479-482: ill

Diffusion welding technology for 6H-SiC substrates
Korolkov, Oleg; **Rang, Toomas** BEC'98 : the 6th Biennial Conference on Electronics and Microsystems Technology, October 7-9, 1998, Tallinn, Estonia : proceedings 1998 / p. 251-252: ill

Diffusion welding technology for wide bandgap materials
Rang, Toomas; **Korolkov, Oleg** Proceedings of the European COPEX Seminar, June 17-19, 1997, Vienna, Austria 1997 / p. 124-127

DLTS measurements on 4H-SiC JBS-diodes with boron implanted local p-n junctions
Ivanov, Pavel; **Korolkov, Oleg**; Samsonova, Tatyana; **Sleptšuk, Natalja**; Potapov, Alexander; **Toompuu, Jana**; **Rang, Toomas** Materials science forum 2011 / p. 409-412 https://www.researchgate.net/publication/272046403_DLTS_measurements_on_4H-SiC_JBS-diodes_with_boron_implanted_local_p-n_junctions

A DLTS study of 4H-SiC-based p-n junctions fabricated by boron implantation
Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; **Korolkov, Oleg**; **Sleptšuk, Natalja** Semiconductors 2011 / p. 1306-1310 : ill https://doi.org/10.1134/S1063782611100101

Electron microscopy study of contact layers in n-type 4H-SiC after diffusion welding
Korolkov, Oleg; **Sleptšuk, Natalja**; Sitnikova, A.; **Rang, Toomas** BEC 2008 : 2008 International Biennial Baltic Electronics Conference : proceedings of the 11th Biennial Baltic Electronics Conference : Tallinn University of Technology : October 6-8, 2008,

Tallinn, Estonia 2008 / p. 91-94 : ill

Experimental study of surface distortions in silicon carbide caused by diffusion welding
Mizsei, Janos; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** BEC 2012 : 2012 13th Biennial Baltic Electronics Conference : proceedings of the 13th Biennial Baltic Electronics Conference : October 3-5, 2012, Tallinn, Estonia 2012 / p. 53-56 : ill

Formation of Diffusion welded Al contacts to semiconductor silicon carbide
Korolkov, Oleg 2004

Formation of large area Al contacts on 6H- and 4H-SiC substrates
Korolkov, Oleg; **Rang, Toomas** Abstracts of the 3rd European Conference on Silicon Carbide and Related Materials : ECSCRM'2000 : Sept. 3-7, 2000, Kloster Banz, Germany 2000 / p. 188 https://www.scientific.net/MSF.353-356.603

Formation of large area Al contacts on 6H- and 4H-SiC substrates
Korolkov, Oleg; **Rang, Toomas** Silicon Carbide and Related Materials : ECSCRM2000 : proceedings of the 3rd European Conference on Silicon Carbide and Related Materials : Kloster Banz, Germany, September 2000 2001 / p. 603-606 : ill

GaAs based diffusion welded high voltage diode stacks [Electronic resource]
Toompuu, Jana; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Voitovitš, Viktor**; **Rang, Toomas** IEEE International Conference on Semiconductor Electronics CD-ROM Proceedings 2010 / [4] p https://ieeexplore.ieee.org/document/5549505

High quality metal ceramic interfaces using diffusion welding technology
Korolkov, Oleg; **Rang, Toomas** Proceedings of the ASDAM'96, Oct. 20-24, 1996, Bratislava, Slovakia 1996 / p. 309-312

High voltage diffusion welded stacks on the basis of SiC Schottky diodes
Korolkov, Oleg; **Sleptšuk, Natalja**; **Annus, Paul**; **Land, Raul**; **Rang, Toomas** ICSRM 2015 : program guide 2015 / p. 73

High-voltage diffusion welded stacks on the basis of SiC Schottky diodes
Korolkov, Oleg; **Sleptšuk, Natalja**; **Annus, Paul**; **Land, Raul**; **Rang, Toomas** Silicon carbide and related materials 2015 (ICSRM 2015) : selected, peer reviewed papers from the 16th International Conference on Silicon Carbide and Related Materials, October 4-9, 2015, Giardini Naxos, Italy 2016 / p. 790-794 : ill https://doi.org/10.4028/www.scientific.net/MSF.858.790 Conference Proceedings at Scopus Article at Scopus

Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes
Kozlovski, Vitali V.; **Korolkov, Oleg**; Davydovskaya, Klavdia S.; Lebedev, Alexander A.; Levinshteĭn, Michael E.; **Sleptšuk, Natalja**; Strel'Chuk, Anatolii M.; **Toompuu, Jana** Technical Physics Letter 2020 / p. 287 - 289 https://doi.org/10.1134/S1063785020030244 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Interpretation of some physical parameters of SiC Schottky interfaces manufactured by diffusion welding technology
Rang, Toomas; **Korolkov, Oleg**; Ljutov, Jevgeni Proceedings of the Estonian Academy of Sciences. Engineering 2004 / 3, p. 179-184

Investigation of additional states in the silicon carbide surface after diffusion welding
Mizsei, Janos; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** ICSCRM2011 : Cleveland Ohio, USA, September 11-16, 2011 : abstracts 2011 / p. 356 : ill
https://www.researchgate.net/publication/269377410_Investigation_of_Additional_States_in_the_Silicon_Carbide_Surface_after_Diffusion_Welding

Investigation of deep level centers in i- and n-layers of GaAs pin-diodes
Toompuu, Jana; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Rang, Toomas** BEC 2014 : 2014 14th Biennial Baltic Electronics Conference : proceedings of the 14th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 6-8, 2014, Tallinn, Estonia 2014 / p. 25-28 : ill

Investigation of p-i-n GaAs structures by DLTS method
Toompuu, Jana; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Rang, Toomas** Elektronika ir elektrotechnika = Electronics and electrical engineering 2010 / 4, p. 51-54 : ill https://www.researchgate.net/publication/267372152_Investigation_of_p-i-n_GaAs_structures_by_DLTS_method

Investigation of subcontact layers in SiC after diffusion welding
Korolkov, Oleg; **Kuznetsova, Natalja**; Sitnikova, A.; **Viljus, Mart**; **Rang, Toomas** Silicon carbide and related materials 2007 / p. 100 https://www.scientific.net/MSF.600-603.647

Investigation of subcontact layers in SiC after diffusion welding
Korolkov, Oleg; **Kuznetsova, Natalja**; Sitnikova, A.; **Viljus, Mart**; **Rang, Toomas** Silicon carbide and related materials 2007 2009

/ p. 647-650

Investigation of the combined stress and strain situation in diffusion welded rectifying elements
Korolkov, Oleg; **Rang, Toomas**; **Kurel, Raido** Surface treatment VI 2003 / p. 307-316 https://www.witpress.com/elibrary/wit-transactions-on-engineering-sciences/39/1441

Investigation of the graphene-on-silicon-carbide and CVD graphene as a basis for bioimpedance sensor applications : poster
Sleptšuk, Natalja; **Land, Raul**; **Toompuu, Jana**; **Lebedev, Alexander A.**; Davydov, Valery; Eliseyev, Ilya; Kalinina, Evgenia; **Korolkov, Oleg**; **Rang, Toomas** ePosters 2018 / 1 p.: ill https://cdn.technologynetworks.com/ep/pdfs/natalja-sleptsuk-a-raul-land-a-jana-toompuu-a-alexander-lebedev-b-valery-davydov-b-ilya-eliseyev-b.pdf

Investigation of the intermediate layer in the metal-silicon carbide contact obtained by diffusion welding = Difusioonkeevitusega valmistatud metalli ja ränikarbiidi vahelise üleminekuala vahekihi uurimine
Sleptšuk, Natalja 2011 https://www.ester.ee/record=b2692547*est

Large area 4H-SiC power Schottky diode
Rang, Toomas; **Korolkov, Oleg**; **Pikkov, Mihhail** Abstracts of the 3rd International Conference and Exhibition Micro Materials : MicroMat2000 : April 17-19, 2000, Berlin, Germany 2000 / p. 303-304

Large area 4H-SiC power Schottky diode
Rang, Toomas; **Korolkov, Oleg**; **Pikkov, Mihhail** Proceedings of the 3rd International Conference and Exhibition Micro Materials : MicroMat2000 : April 17-19, 2000, Berlin, Germany 2000 / p. 890-893

Large area 6H-SiC Schottky diode
Rang, Toomas; **Korolkov, Oleg**; **Pikkov, Mihhail** Proceedings of the Estonian Academy of Sciences. Engineering 2000 / 2, p. 155-159 : ill https://artiklid.elnet.ee/record=b1004045*est

Large area high quality interfaces to SiC substrates - technology and modelling
Rang, Toomas; **Korolkov, Oleg**; **Kurel, Raido**; **Pikkov, Mihhail** Materials mechanics, fracture mechanics, micro mechanics 1999 / p. 574-579: ill

Leakage currents in 4H-SiC JBS diodes
Ivanov, Pavel; **Korolkov, Oleg**; **Sleptšuk, Natalja** Semiconductors 2012 / p. 397-400 : ill https://link.springer.com/article/10.1134/S106378261203013X

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons
Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Semiconductors 2019 / p. 975–978 https://doi.org/10.1134/S1063782619070133 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Metallization technologies for wide band-gap semiconductor substrates : (invited paper)
Rang, Toomas; **Korolkov, Oleg**; **Pikkov, Mihhail** Proceedings of the 6th Nexuspan Workshop Microsystems Technology Activities in Baltic Region : 23-24 April, 1999, Vilnius, Lithuania 1999 / p. 27-30

Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p^+-pin-n^+ structures and result of analysis
Toompuu, Jana; **Sleptšuk, Natalja**; **Korolkov, Oleg**; **Rang, Toomas** BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 35-38 : ill http://www.ester.ee/record=b2150914*est

Polytypic heterojunctions for wide bandgap semiconductor materials
Shenkin, Mikhail; **Korolkov, Oleg**; **Rang, Toomas**; **Rang, Galina** Materials characterization VII 2015 / p. 273-282 : ill

Preliminary investigation of diffusion welded contacts to p-type 6H-SiC
Korolkov, Oleg; **Rang, Toomas**; Kuznetsova, Natalja; Ruut, Jana BEC 2002 : proceedings of the 8th Biennial Baltic Electronics Conference : October 6-9, 2002, Tallinn, Estonia 2002 / p. 55-56 : ill

SiC JBS diode symmetrical voltage doubler represented as the diffusion-welded stack
Korolkov, Oleg; **Land, Raul**; **Toompuu, Jana**; **Sleptšuk, Natalja**; **Rang, Toomas** Silicon carbide and related materials 2017 : ICSCRM 2017 : selected, peer reviewed papers from the 2017 International Conference on Silicon Carbide and related materials, September 17-22, 2017, Washington, DC, USA 2018 / p. 862–865 : ill https://doi.org/10.4028/www.scientific.net/MSF.924.862 Conference Proceedings at Scopus Article at Scopus

SIC schottky diode rectifier bridge represented as the diffusion-welded stack
Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Land, Raul**; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas**

Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 697-700 : ill https://doi.org/10.4028/www.scientific.net/MSF.897.697 Conference proceedings at Scopus Article at Scopus

SIC schottky diode rectifier bridge represented as the diffusion-welded stack
Korolkov, Oleg; **Land, Raul**; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 42

Some comparative properties of diffusion-welded contacts to 6H and 4H silicon carbide
Korolkov, Oleg; **Rang, Toomas** Silicon Carbide and Related Materials 2001 : ICSCRM2001 : proceedings of the International Conference on Silicon Carbide and Related Materials 2001, Tsukuba, Japan, October 28 - November 2, 2001. Part 2 2002 / p. 941-944 : ill

Some of comparative properties of diffusion welded contacts to 6H- and 4H-silicon carbide
Korolkov, Oleg; **Rang, Toomas** International Conference on Silicon Carbide and Related Materials 2001 - ICSCRM2001 - October 28-November 2, 2001 (Epochal Tsukuba, Ibaraki, Japan) : technical digest 2001 / p. 625-626 : ill https://www.researchgate.net/publication/250340293_Some_Comparative_Properties_of_Diffusion-Welded_Contacts_to_6H_and_4H_Silicon_Carbide

Study of surface defects in 4H-SiC Schottky diodes using a scanning Kelvin probe
Mizsei, Janos; **Korolkov, Oleg**; **Toompuu, Jana**; **Rang, Toomas** The 9th European Conference on Silicon Carbide and Related Materials : abstract book : St. Petersburg Russia, 2-6 September, 2012 2012 / 2 p. : ill

Study of surface defects in 4H-SiC Schottky diodes using a scanning Kelvin probe
Mizsei, Janos; **Korolkov, Oleg**; **Toompuu, Jana**; **Mikli, Valdek**; **Rang, Toomas** Silicon Carbide and Related Materials 2012 : selected peer reviewed papers from the 9th European Conference on Silicon Carbide and Related Materials (ECSCRM 2012), September 2-6, 2012, St. Petersburg, Russian Federation 2013 / p. 677-680 : ill https://doi.org/10.4028/www.scientific.net/MSF.740-742.677 Conference Proceedings at Scopus Article at Scopus Conference Proceedings at WOS Article at WOS

Subcontact layers in LPE structures for forming the ohmic contacts on GaAs semiconductor substrates
Korolkov, Oleg; **Voitovitš, Viktor**; **Rang, Toomas** Abstract book of 13th American Conference on Crystal Growth and Epitaxy : August 12-16, 2001, Burlington, Vermont, USA 2001 / p. 133

The basic parameters of diffusion welded Al Schottky contacts to p- and n-SiC
Korolkov, Oleg; Ruut, Jana; Kuznetsova, Natalja; **Rang, Toomas** Silicon Carbide and Related Materials 2003 2004 / p. 857-860 https://doi.org/10.4028/www.scientific.net/MSF.457-460.857

The dependence of reverse recovery time on barrier capacitance and series on-resistance in Schottky diodes
Veher, Oleksandr; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Korolkov, Oleg**; **Rang, Toomas** Materials and contact characterisation VIII 2017 / p. 15-22 : ill https://doi.org/10.2495/MC170021 Conference proceedings at Scopus Article at Scopus

The diffusion welded contacts in power electronics and electrotechnics
Korolkov, Oleg Telekommunikatsioon '98 : rahvusvahelise telekommunikatsioonipäeva konverentsi ettekannete materjalid, 15. mai 1998 1998 / lk. 84-86: ill

The measurement and tuning of SiC diode voltage doubler represented as diffusion-welded stack [Online resource]
Toompuu, Jana; **Sleptšuk, Natalja**; **Land, Raul**; **Korolkov, Oleg**; **Rang, Toomas** BEC 2018 : 2018 16th Biennial Baltic Electronics Conference (BEC) : proceedings of the 16th Biennial Baltic Electronics Conference, October 8-10, 2018 2018 / 4 p.: ill https://doi.org/10.1109/BEC.2018.8600963

The Schottky parameter test for combined diffusion welded and sputter large area contacts
Korolkov, Oleg; **Kuznetsova, Natalja**; **Rang, Toomas**; Syrkin, A.; Dmitriev, V. Silicon carbide and related materials 2007 / p. 737-740 https://www.scientific.net/MSF.556-557.737

The specificity of solid-phase interaction of aluminium with silicon carbide in the manufacture of diffusion-welded contacts to semiconductor devices
Sleptšuk, Natalja; **Korolkov, Oleg**; **Toompuu, Jana**; **Rang, Toomas**; **Mikli, Valdek** Elektronika ir elektrotechnika = Electronics and electrical engineering 2012 / p. 45-48 : ill https://eejournal.ktu.lt/index.php/elt/article/view/2610

Анализ процессов распросттранения тепла в структурах импульсных силовых приборов вблизи плоскостей спая кремниевых пластин в высоковольтные "столбы"
Glazov, Aleksei; **Korolkov, Oleg** Известия высших учебных заведений. Материалы электронной техники 2012 / с. 65-69 : ил

Исследование p-n-переходов на основе 4H-SiC, изготовленных имплантацией бора, методом нестационарной емкостной спектроскопии
Ivanov, Pavel; Potapov, Alexander; Samsonova, Tatyana; **Korolkov, Oleg**; **Sleptšuk, Natalja** Физика и техника полупроводников 2011 / с. 1358-1362 : ил

Низкотемпературный отжиг слаболегированных слоев n-4H-SiC после облучения быстрыми электронами
Korolkov, Oleg; Kozlovski, Vitali; Lebedev, Alexander; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Физика и техника полупроводников 2019 / с. 991-994 https://doi.org/10.21883/FTP.2019.07.47879.9089